TOSHIBA Transistor Silicon PNP Epitaxial Type

TPCP8603

High-Speed Switching Applications

DC/DC Converters

Strobe Applications

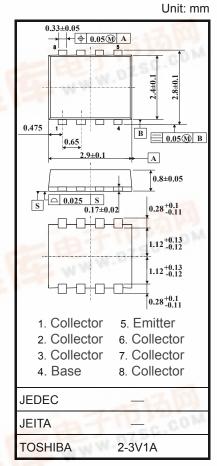
- High DC current gain: $h_{FE} = 120 \sim 300 \text{ (IC} = -0.1 \text{ A)}$
- Low collector-emitter saturation voltage: V_{CE} (sat) = −0.2 V (max)
- High-speed switching: t_f = 120 ns (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-vase voltage		V_{CBO}	-120	V	
Collector-emitter voltage		V_{CEO}	-120	V	
Collector-emitter voltage		V_{EBO}	-7	V	
Collector current	DC (Note 1)	Ic	-1.0	Α	
	Pulsed (Note 1)	I _{CP}	-2.0	Α	
Base current		lΒ	0.1	Α	
Collector power dissipation	t = 10 s	P _C (Note 2)	3.00	W	
	DC	FC (Note 2)	1.25	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

- Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.
- Note 2: Mounted on the FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm²)
- Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.017 g (typ.)



Figure 1. Circuit Configuration

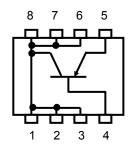
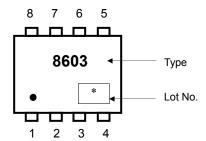
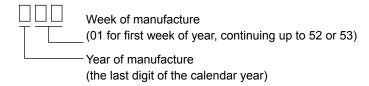


Figure 2. Marking (Note4)



Note 4: ● on the lower left of the marking indicates Pin 1.

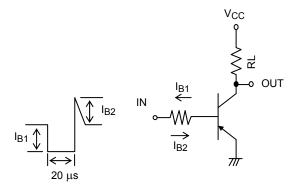
* Weekly code (three digits):



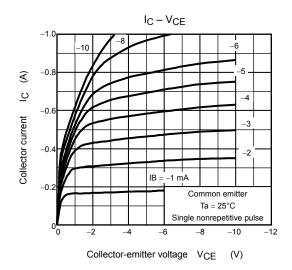
Electrical Characteristics (Ta = 25°C)

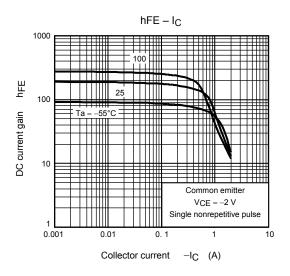
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cutoff current		I _{CBO}	$V_{CB} = -120 \text{ V}, IE = 0$	_	_	-100	nA	
Emitter cutoff current		I _{EBO}	$V_{EB} = -7 \text{ V, } I_{C} = 0$	_	_	-100	nA	
Collector-emitter breakdown voltage		V (BR) CEO	$I_C = -10 \text{ mA}, IB = 0$	-120	_	_	V	
DC current gain		hFE(1)	V _{CE} = -2 V, I _C = -0.1 A	120	_	300		
		hFE(2)	$V_{CE} = -2 \text{ V}, I_{C} = -0.3 \text{ A}$	60	_	_		
Collector-emitter saturation voltage		V _{CE} (sat)	$I_C = -0.3 \text{ A}, IB = -0.01 \text{ A}$	_	_	-0.2	V	
Base-emitter saturation voltage		V _{BE (sat)}	$I_C = -0.3 \text{ A}, IB = -0.01 \text{ A}$	_	_	-1.1	V	
Switching time	Storage time	t _r	See Figure 3 circuit diagram.	_	130	_		
	Storage time	t _{stg}	$V_{CC} \cong 72 \text{ V}, \text{ RL} = 240 \Omega$	_	650	_	ns	
	Fall time	t _f	−IB1 = IB2 = −10 mA	_	120	_		

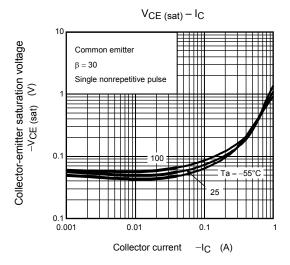
Figure 3. Switching Time Test Circuit & Timing Chart

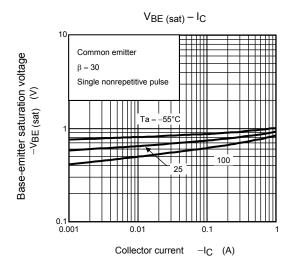


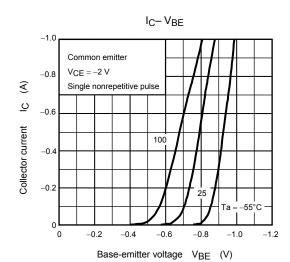
Duty cycle < 1 %





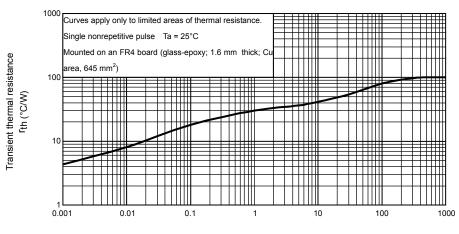






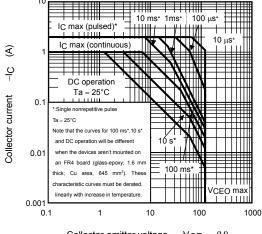
3





Pulse width t_w (S)

Safe Operating Area



Collector-emitter voltage -VCE

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20070701-EN

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